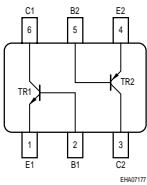


**NPN/PNP Silicon AF Transistor Arrays**

- For AF input stage and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated NPN/PNP transistor in one package
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



**BC846PN**  
**BC846UPN**  
**BC847PN**



Type	Marking	Pin Configuration						Package
BC846PN	1Os	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BC846UPN	1Os	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SC74
BC847PN	1Ps	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage BC846PN/UPN BC847PN	$V_{CEO}$	65 45	V
Collector-emitter voltage BC846PN/UPN BC847PN	$V_{CES}$	80 50	
Collector-base voltage BC846PN/UPN BC847PN	$V_{CBO}$	80 50	
Emitter-base voltage	$V_{EBO}$	6	
Collector current	$I_C$	100	mA
Peak collector current, $t_p \leq 10$ ms	$I_{CM}$	200	
Total power dissipation- $T_S \leq 115^\circ\text{C}$ , BC846PN, BC847PN $T_S \leq 118^\circ\text{C}$ , BC846UPN	$P_{tot}$	250 250	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup> BC846PN, BC847PN BC846UPN	$R_{thJS}$	$\leq 140$ $\leq 130$	K/W

<sup>1</sup>For calculation of  $R_{thJA}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 10\text{ mA}$ , $I_B = 0$ , BC846PN/UPN $I_C = 10\text{ mA}$ , $I_B = 0$ , BC847PN	$V_{(BR)CEO}$	65 45	- -	- -	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ , BC846PN/UPN $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ , BC847PN	$V_{(BR)CBO}$	80 50	- -	- -	
Collector-emitter breakdown voltage $I_C = 10\text{ }\mu\text{A}$ , $V_{BE} = 0$ , BC846PN/UPN $I_C = 10\text{ }\mu\text{A}$ , $V_{BE} = 0$ , BC847PN	$V_{(BR)CES}$	80 50	- -	- -	
Emitter-base breakdown voltage $I_E = 1\text{ }\mu\text{A}$ , $I_C = 0$	$V_{(BR)EBO}$	6	-	-	
Collector-base cutoff current $V_{CB} = 50\text{ V}$ , $I_E = 0$ $V_{CB} = 30\text{ V}$ , $I_E = 0$ , $T_A = 150^\circ\text{C}$	$I_{CBO}$	- -	- -	0.015 5	$\mu\text{A}$
DC current gain- $I_C = 10\text{ }\mu\text{A}$ , $V_{CE} = 5\text{ V}$ $I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$	$h_{FE}$	- 200	250 290	- 450	-
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$ , $I_B = 5\text{ mA}$	$V_{CEsat}$	- -	90 200	300 650	mV
Base emitter saturation voltage <sup>-1)</sup> $I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$ , $I_B = 5\text{ mA}$	$V_{BEsat}$	- -	700 900	- -	
Base-emitter voltage <sup>-1)</sup> $I_C = 2\text{ mA}$ , $V_{CE} = 5\text{ V}$ $I_C = 10\text{ mA}$ , $V_{CE} = 5\text{ V}$	$V_{BE(ON)}$	580 -	660 -	750 820	

<sup>1)</sup>Pulse test:  $t = 300\mu\text{s}$ ,  $D = 2\%$

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b>					
Transition frequency $I_C = 10\text{ mA}, V_{CE} = 5\text{ V}, f = 100\text{ MHz}$	$f_T$	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}, f = 1\text{ MHz}$	$C_{cb}$	-	1.5	-	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}, f = 1\text{ MHz}$	$C_{eb}$	-	8	-	
Short-circuit input impedance $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}$	$h_{11e}$	-	4.5	-	k $\Omega$
Open-circuit reverse voltage transf. ratio $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}$	$h_{12e}$	-	2	-	$10^{-4}$
Short-circuit forward current transf. ratio $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}$	$h_{21e}$	-	330	-	-
Open-circuit output admittance $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}$	$h_{22e}$	-	30	-	$\mu\text{S}$

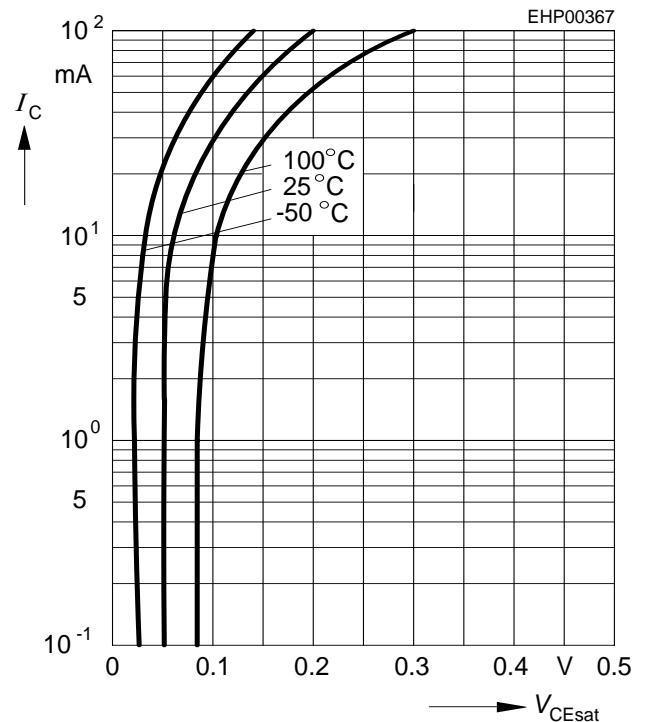
**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 5\text{ V}$



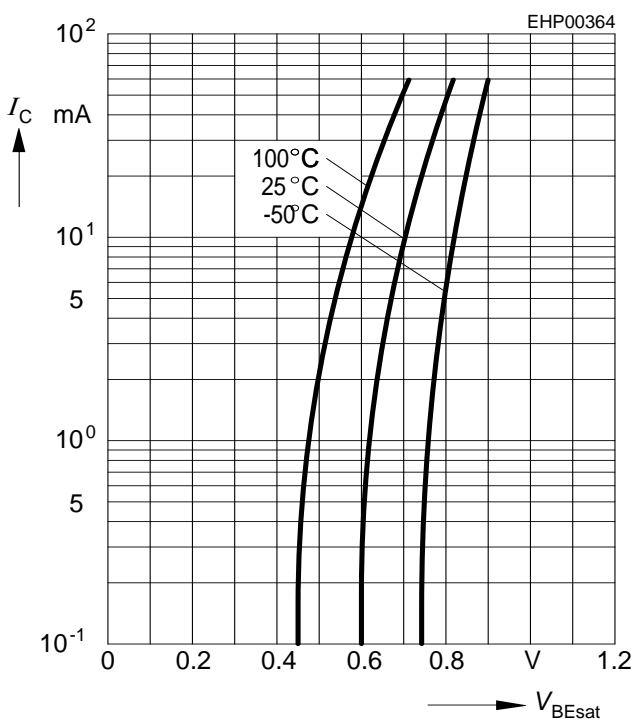
**Collector-emitter saturation voltage**

$I_C = f(V_{CEsat}), h_{FE} = 20$



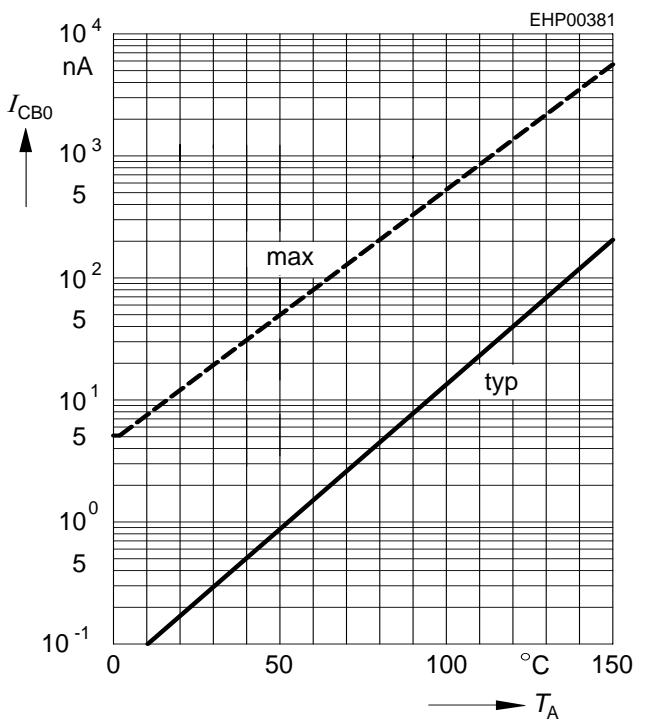
**Base-emitter saturation voltage**

$I_C = f(V_{BEsat}), h_{FE} = 20$



**Collector cutoff current  $I_{CBO} = f(T_A)$**

$V_{CBO} = 30\text{ V}$



Transition frequency  $f_T = f(I_C)$

$V_{CE} = 5\text{ V}, f = 100\text{ MHz}$



Collector-base capacitance  $C_{cb} = f(V_{CB})$

Emitter-base capacitance  $C_{eb} = f(V_{EB})$



Total power dissipation  $P_{tot} = f(T_S)$

BC846PN, BC847PN



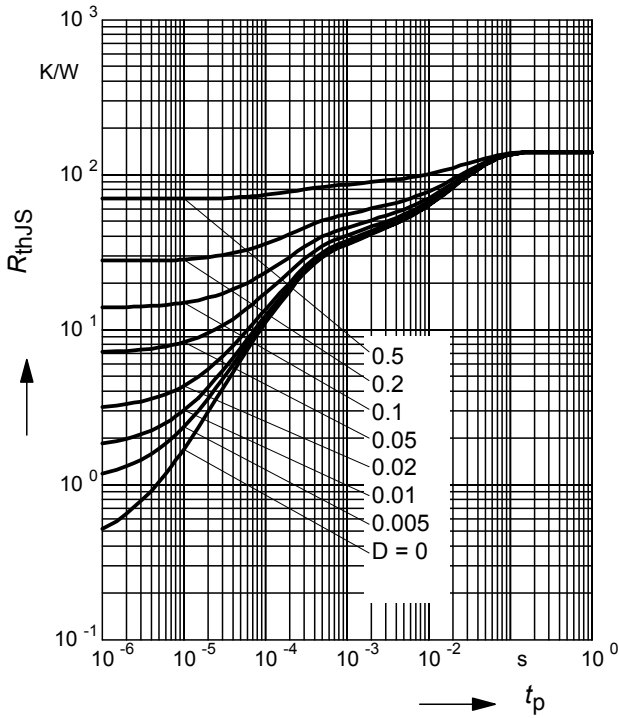
Total power dissipation  $P_{tot} = f(T_S)$

BC846UPN



**Permissible Pulse Load  $R_{thJS} = f(t_p)$**

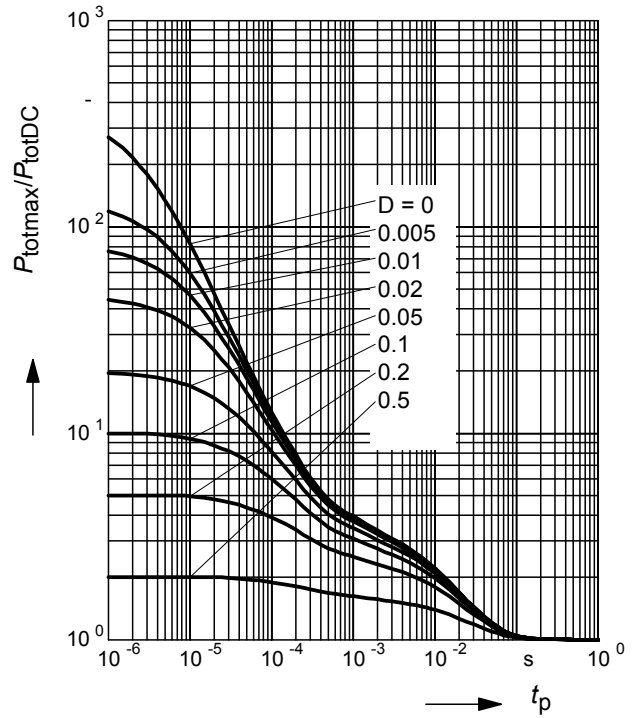
BC846PN, BC847PN



**Permissible Pulse Load**

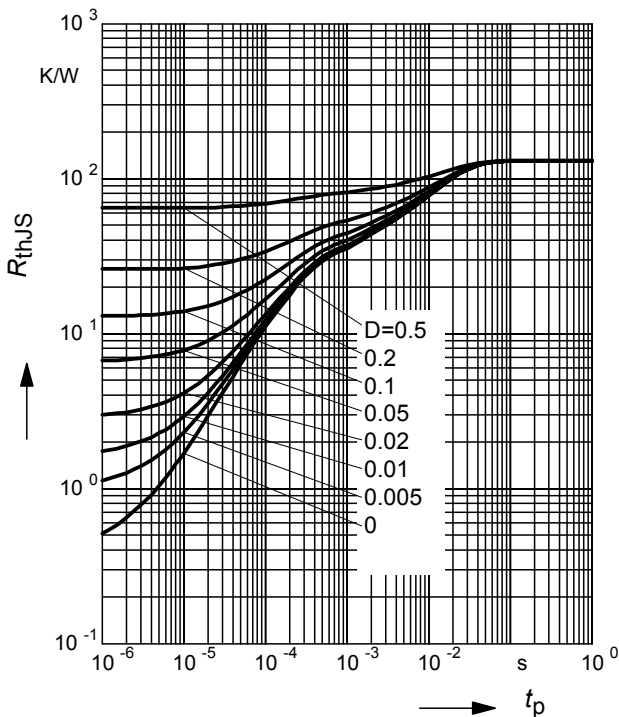
$P_{totmax}/P_{totDC} = f(t_p)$

BC846PN, BC847PN



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

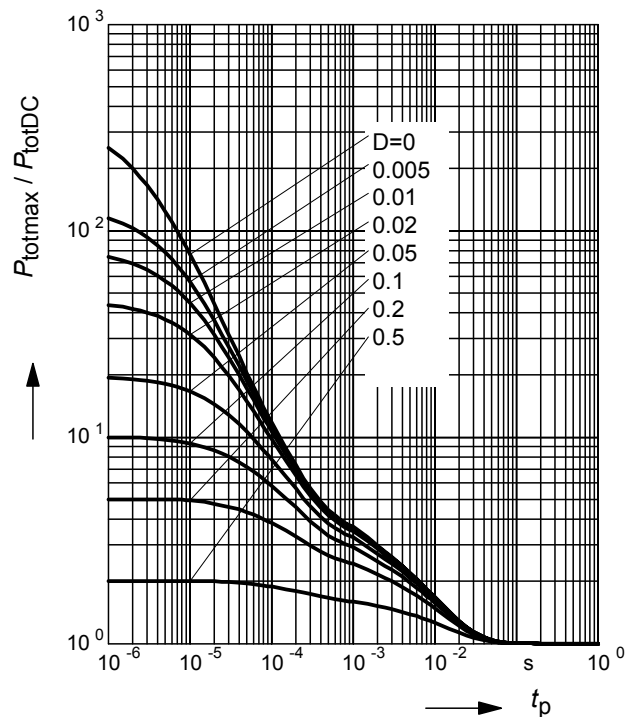
BC846UPN



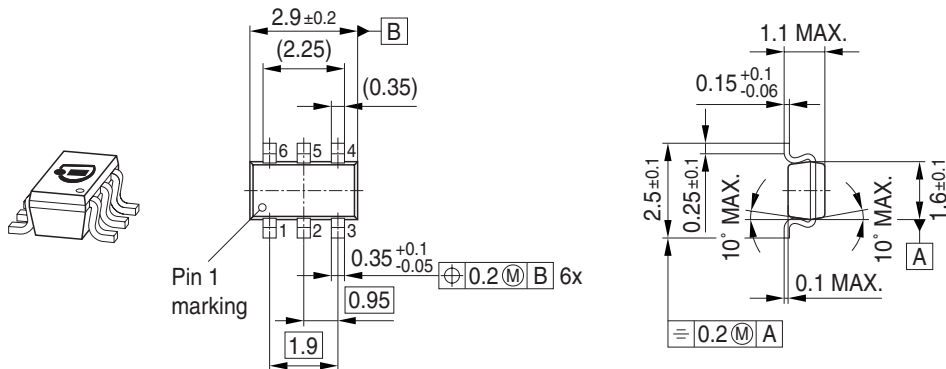
**Permissible Pulse Load**

$P_{totmax}/P_{totDC} = f(t_p)$

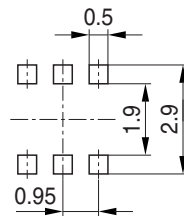
BC846UPN



Package Outline



Foot Print



Marking Layout (Example)

Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

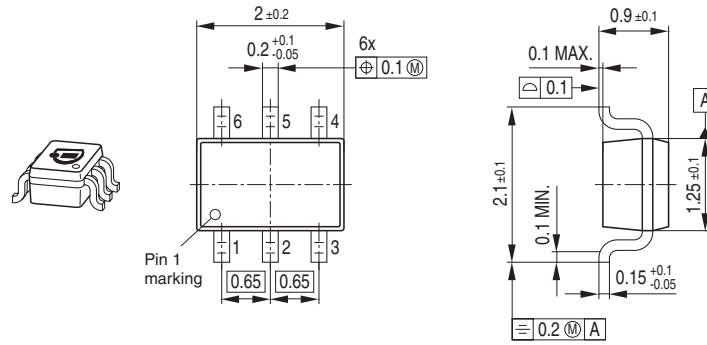
Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





### Package Outline



### Foot Print



### Marking Layout (Example)

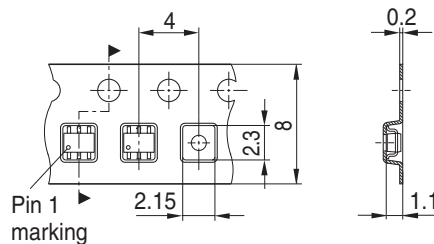
Small variations in positioning of Date code, Type code and Manufacturer are possible.



### Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



**Edition 2009-11-16**

**Published by  
Infineon Technologies AG  
81726 Munich, Germany**

**© 2009 Infineon Technologies AG  
All Rights Reserved.**

### **Legal Disclaimer**

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

### **Information**

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

### **Warnings**

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)

[>>点击查看相关商品](#)